

/ Descriptions

WR0<5 SQS Silicon PNP transistor in a TO-92 Plastic Package.

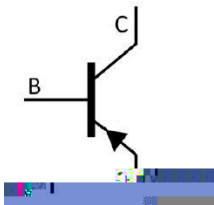
/ Features

/ /
Low noise, high DC current gain, high breakdown voltage.

/ Applications

Low noise audio amplifier applications.

/ Equivalent Circuit



/ Pinning



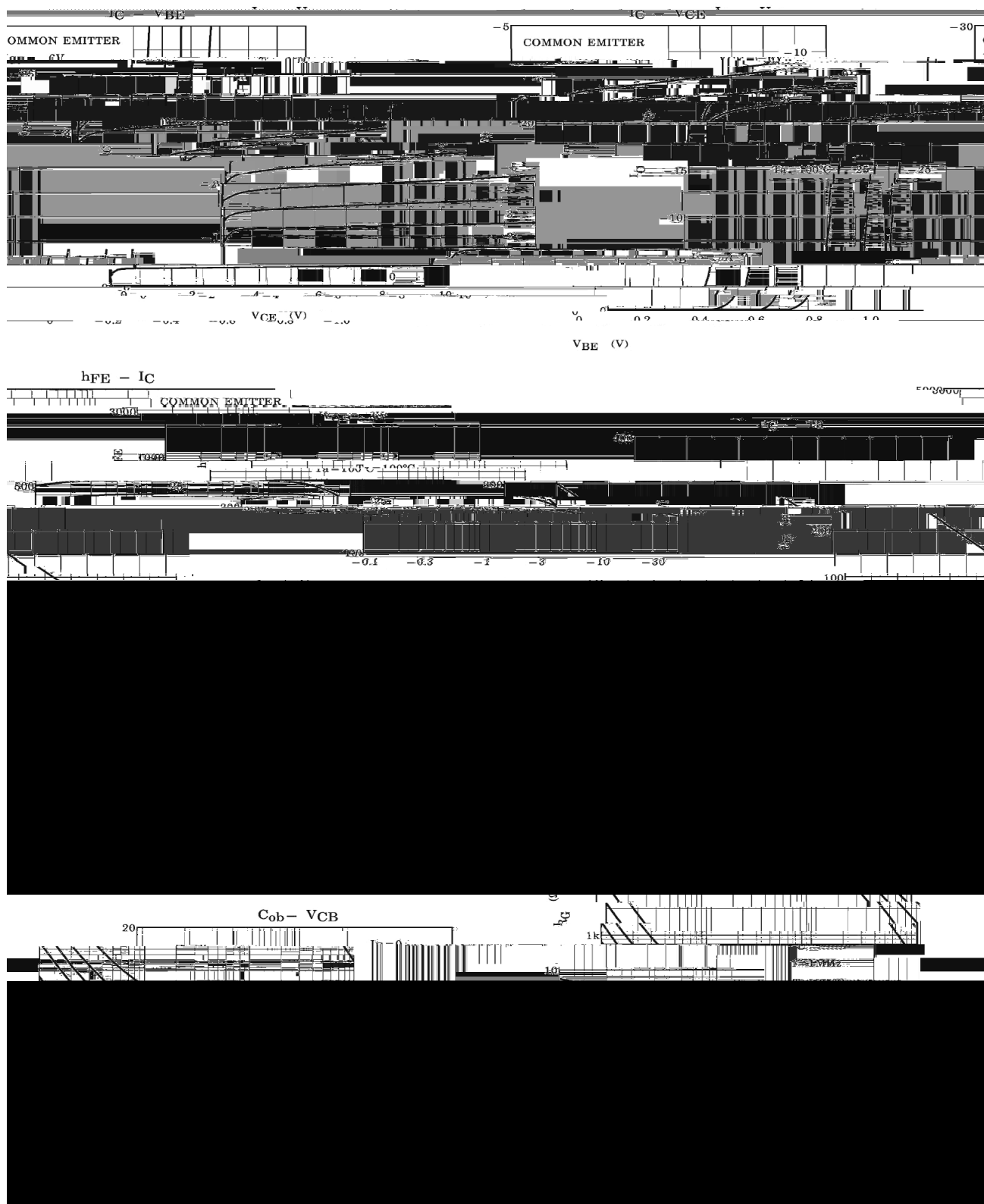
PIN1 Base PIN 2 Collector PIN 3 Emitter

/ hFE Classifications & Marking

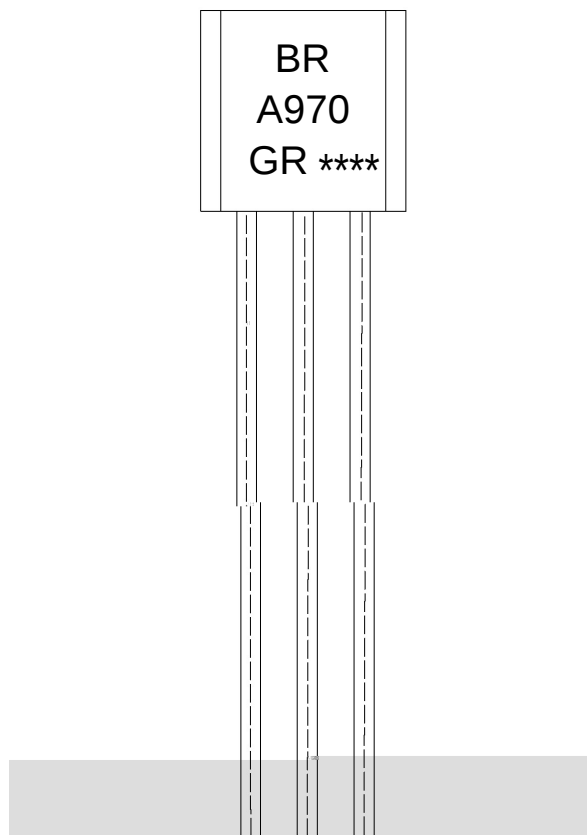
h_{FE} Classifications Symbol	GR	BL
h_{FE} Range	200~400	350~700

Parameter		Symbol	Rating	Unit
Collector to Base Voltage		V_{CBO}	-120	V
Collector to Emitter Voltage		V_{CEO}	-120	V
Emitter to Base Voltage		V_{EBO}	-5.0	V
Collector Current - Continuous		I_C	-100	mA
Emitter Current – Continuous		I_E	100	mA
Collector Power Dissipation		P_C	300	mW
Junction Temperature		T_j	152 591iw560.J/TT7 161 Tf28 TD0107	

/ Electrical Characteristic Curve



/ Marking Instructions



EU:

D<: 3

JU: h_{FE}

Note:

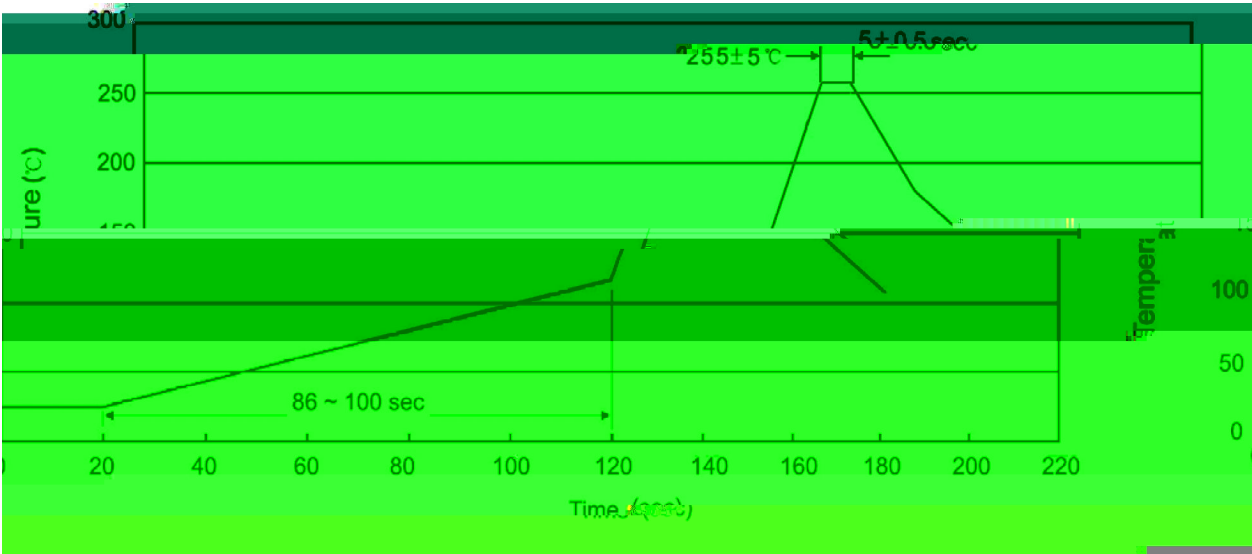
BR: Company Code.

A970: Product Type Code.

GR: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150 $\frac{3}{8}$

60 90sec;
- 2

255 $\pm$ 5 $\frac{3}{8}$

5 $\pm$ 0.5sec;
- 3

2 10 $\frac{3}{8}$ /sec.
- 1.Preheating:25~150 $\frac{3}{8}$, Time:60~90sec.

2.Peak Temp.:255 $\pm$ 5 $\frac{3}{8}$, Duration:5 $\pm$ 0.5sec.

3. Cooling Speed: 2~10 $\frac{3}{8}$ /sec.

/ Resistance to Soldering Heat Test Conditions

270 $\pm$ 5 $\frac{3}{8}$

10 $\pm$ 1 sec.

Temp:270 $\pm$ 5

Time:10 $\pm$ 1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm3)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

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